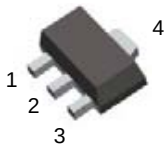
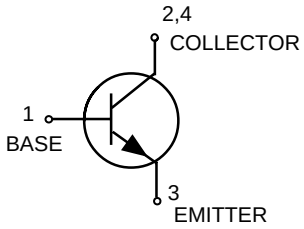
PNPSURFACEMOUNTTRANSISTOR

L2SB882Q
L2SB882P

- We declare that the material of product compliance with RoHS requirements.



SOT-89



DEVICE MARKING AND ORDERING INFORMATION

Device	Marking	Shipping
L2SB882Q	82Q	2500/Tape&Reel
L2SB882P	82P	2500/Tape&Reel

MAXIMUM RATINGS(Ta=25°C)

Parameter	Symbol	Limits	Unit
Collector-base voltage	V_{CBO}	40	V
Collector-emitter voltage	V_{CEO}	30	V
Emitter-base voltage	V_{EBO}	6	V
Peak Pulse Current	I_{CM}	3	A
Collector power dissipation	P_C	0.5	W
Junction temperature	Tj	150	°C
Storage temperature	Tstg	–55 to 150	°C

ELECTRICAL CHARACTERISTICS(Ta=25°C)

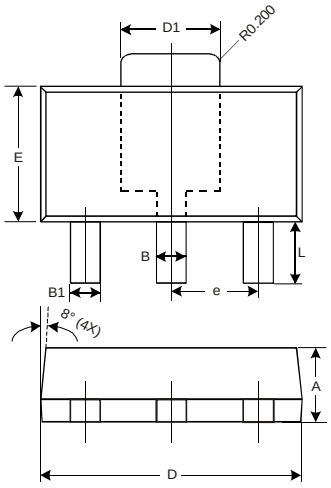
Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-base breakdown voltage	BV_{CBO}	40	–	–	V	I_C= 100μA
Collector-emitter breakdown voltage	BV_{CEO}	30	–	–	V	I_C= 10mA
Emitter-base breakdown voltage	BV_{EBO}	6	–	–	V	I_E= 100μA
Collector cutoff current	I_{CBO}	–	–	1	μA	V_{CB}= 40V
Collector cutoff current	I_{CEO}	–	–	10	μA	V_{CB}= 30V
Emitter cutoff current	I_{EBO}	–	–	1	μA	V_{EB}= 6V
Collector-emitter saturation voltage	$V_{CE(sat)}$	–	–	0.5	V	I_C/I_B=2A/0.2A
Base-emitter saturation voltage	$V_{BE(sat)}$	–	–	1.5	V	I_C/I_B=2A/0.2A
DC current transfer ratio	$h_{FE(1)}$	100	–	320	–	V_{CE}=2V, I_C=1A
DC current transfer ratio	h_{FE}	32	–	–	–	V_{CE}=2V, I_C=100mA
Transition frequency	f_T	50	–	–	MHz	V_{CE}= 5V, I_E=0.1A, f =10MHz

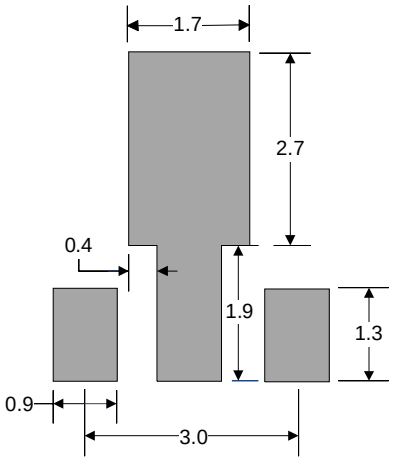
$h_{FE(1)}$ values are classified as follows :

Item(*)	Q	P
h_{FE}	100~200	160~320

L2SB882Q
L2SB882P

SOT-89



Unit: mm

SOT89-3L			
Dim	**Min**	**Max**	**Typ**
A	1.40	1.60	1.50
B	0.45	0.55	0.50
B1	0.37	0.47	0.42
C	0.35	0.43	0.38
D	4.40	4.60	4.50
D1	1.50	1.70	1.60
E	2.40	2.60	2.50
e	—	—	1.50
H	3.95	4.25	4.10
L	0.90	1.20	1.05
All Dimensions in mm